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RD50 HV-CMOS Meeting

# RD50-MPW4 Allpix<sup>2</sup> Simulations

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## Allpix<sup>2</sup>

- Monte Carlo Detector Simulation Framework
- Geant4 utilized to build detector geometry and deposit energy in detector due incoming particle beam
- Modular framework
  - Build geometry
  - Apply E-field (simple linear field approximation → advanced fields from TCAD)
  - Deposit charge
  - Propagate charge (drift in E-field and diffusion)
  - Collect at surface / implant
  - Digitize
  - Interpret and output to ROOT files
- Talk by Simon Spannagel at DRD3 week: <https://indico.cern.ch/event/1402825/contributions/5998273/>

## Allpix<sup>2</sup> Usage

- We need 3 config files (key value pairs, pretty similar to Corryvreckan)
  - 1) Detector model specifies material, thickness, pixel pitch, number of pixels, ...
  - 2) Place (several) detectors in world volume in geometry-file
  - 3) Define simulation chain (module by module) in config file
- Allpix<sup>2</sup> executed via CLI with something like “allpix -c best-simulation-ever.conf”

```
mpw4 > 0 rd50_mpw4.conf
1 type = "monolithic"
2 geometry = "pixel"
3
4 number_of_pixels = 64 64
5 # Pitch of one individual pixel (column and row pitch)
6 pixel_size = 62um 62um
7
8 # Thickness of the active sensor material
9 sensor_thickness = 300um
10 # Excess sensor material outside of the active pixel matrix
11 # Specifying one value will add the excess to all four sides
12 #sensor_excess_bottom = 2mm
13
14
15 # [implant]
16 # type = frontside
17 # size = 43um 43um 20um
18
19 # [support]
20 # thickness = 1.5mm
21 # size = 12cm 10cm
22 # location = sensor
23 # material = plexiglass
24 #offset = -4cm 0
25 #hole size = 4.2mm 4.2mm
26 #hole offset = -4cm 0
27
28
29 [[telescope0]]
30 type = "adanium"
31 position = 0mm 0mm 0mm
32 orientation_mode = "xyz"
33 orientation = 0deg 0deg 0deg
34 alignment_precision_position = 1.5mm 1.5mm 1.5mm
35 alignment_precision_orientation = 5deg 5deg 5deg
36
37 [[telescope1]]
38 type = "adanium"
39 position = 0mm 0mm 26mm
40 orientation_mode = "xyz"
41 orientation = 0deg 0deg 0deg
42 alignment_precision_position = 1.5mm 1.5mm 1.5mm
43 alignment_precision_orientation = 5deg 5deg 5deg
44
45 [[telescope2]]
46 type = "adanium"
47 position = 0mm 0mm 52mm
48 orientation_mode = "xyz"
49 orientation = 0deg 0deg 0deg
50 alignment_precision_position = 1.5mm 1.5mm 1.5mm
51 alignment_precision_orientation = 5deg 5deg 5deg
52
53
54 [[mpw4]]
55 type = "rd50_mpw4"
56 position = 0 0 137mm
57 orientation_mode = "xyz"
58 orientation = 0deg 0deg 0deg
59 alignment_precision_position = 1.5mm 1.5mm 1.5mm
60 alignment_precision_orientation = 5deg 5deg 5deg
```

```
[[AllPix]]
log_level = "WARNING"
log_format = "DEFAULT"
number_of_events = 2000000
# workers = 80
detectors_file = "detectors.conf"
root_file = "sim_investigateNoDiff.root"
output_directory = "/scratch/bpisl/mpw4_sim"

[[GeometryBuilderGeant4]]
world_material = "air"

[[DepositionGeant4]]
physics_list = FTFP_BERT_LIV
particle_type = "e-"
source_energy = 4.2GeV
source_position = 0 0 -20mm
source_type = "beam"
beam_direction = 0 0 1
beam_size = 2.5mm
number_of_particles = 1
output_plots = true

[[ElectricFieldReader]]
name = "mpw4"
model = "linear"
bias_voltage = -190V
depletion_voltage = -200V
output_plots = true

[[GenericPropagation]]
name = "mpw4"
temperature = 0.1K
# charge_per_step = 10
output_plots = true
# output_linegraphs = true
# output_linegraphs_collected = true
# output_animations = true

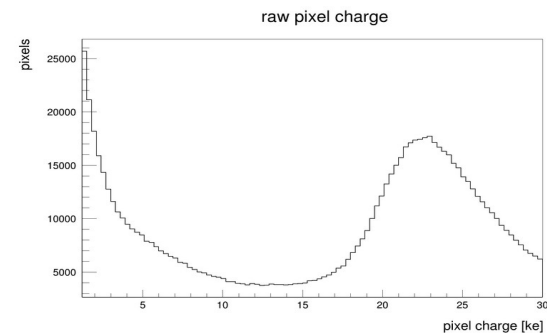
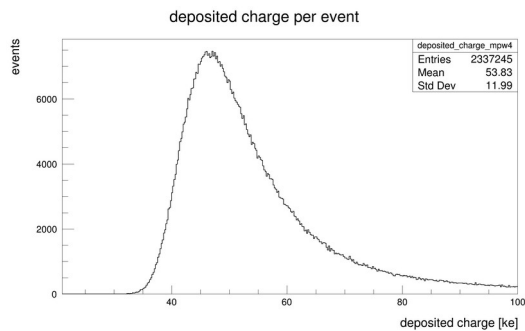
[[PulseTransfer]]
name = "mpw4"
output_plots = true

#max_depth_distance = 5um

[[DefaultDigitizer]]
name = "mpw4"
output_plots = true
electronics_noise = 550e
threshold = 2800e
threshold_smearing = 30e
# qdc_resolution = 0
# qdc_offset = -2800e
# qdc_slope = 3200e
```

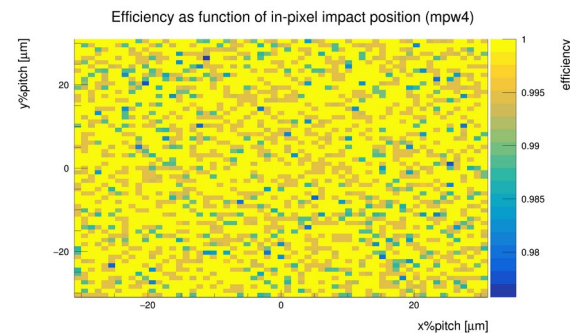
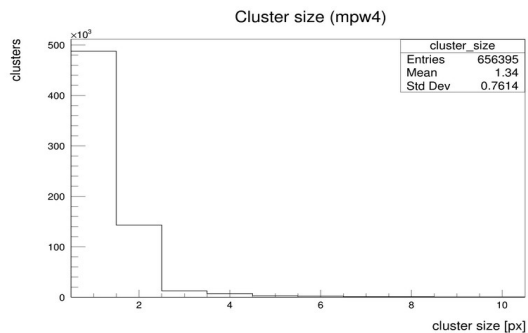
# Allpix<sup>2</sup> Possibilities

Deposited charge  
(e<sup>-</sup> / hole pairs)  
per incident particle



Charge propagated  
to pixel

Cluster size



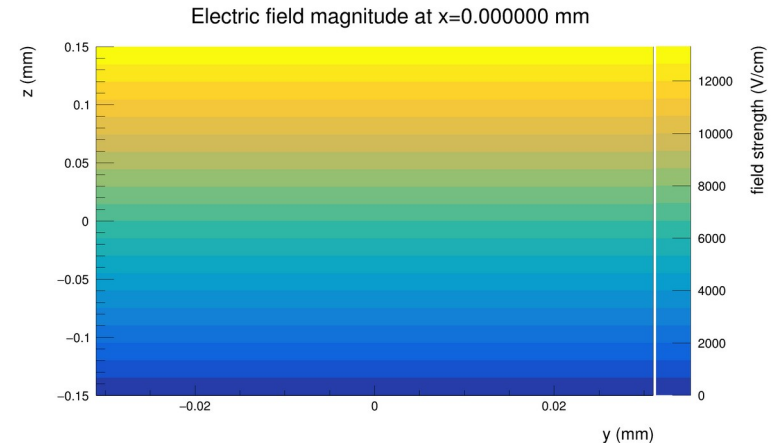
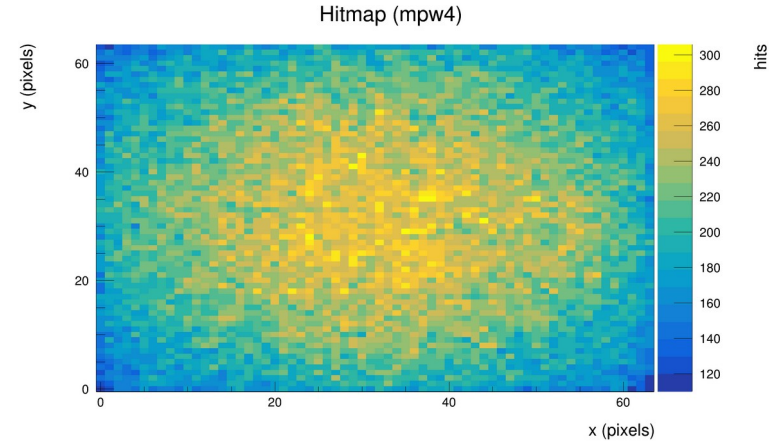
Efficiency  
- In-Pixel  
- Full Chip

## Simulation Goals

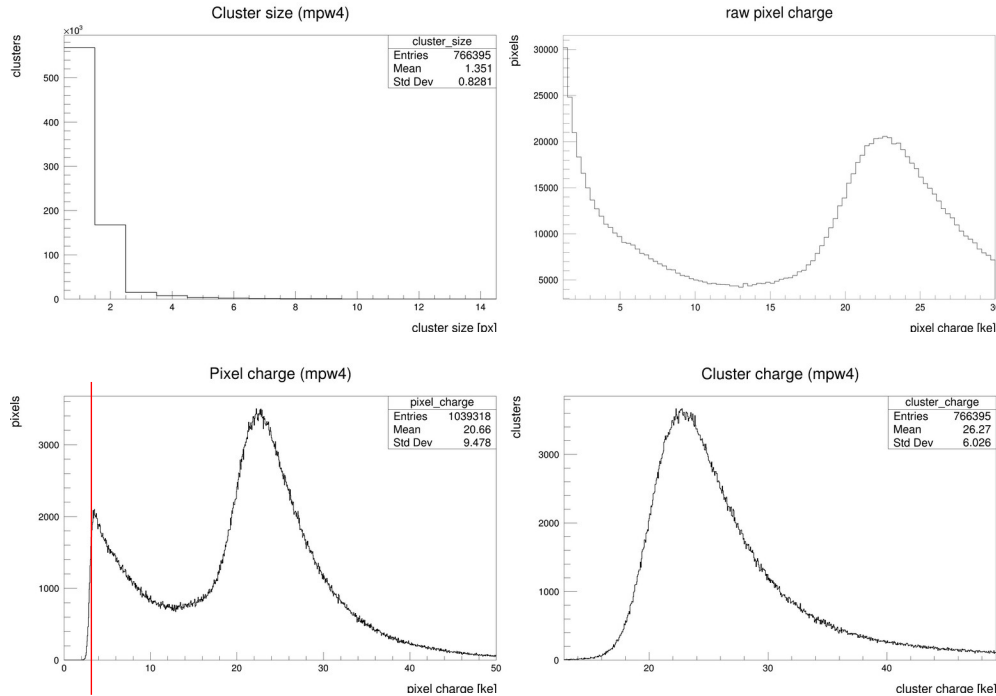
- Do we understand our sensor properly?
  - Depletion
  - Threshold
  - ...
- Benchmark simulation with test-beam results
- Tune simulation parameters → Improve characteristics of MPW4
  - Spatial resolution (charge sharing, cluster position calculation)
- Find crucial parameters as „design goals“ for possible next iteration

## Current Setup

- DESY beam
  - 4.2 GeV electrons in air
- Linear electric field
  - Depletion voltage = -200V
  - Bias voltage = -200V
  - Only in z-direction; No lateral component
- Charge collection full pixel surface
  - No deep N-Well implant
- Threshold: 3000e-
  - $V_{Thr} \sim 30 - 40\text{mV}$
- No telescope only MPW4 in 2cm distance from particle source
  - Faster than using actual test-beam distance (less scattering in air needs to be simulated)



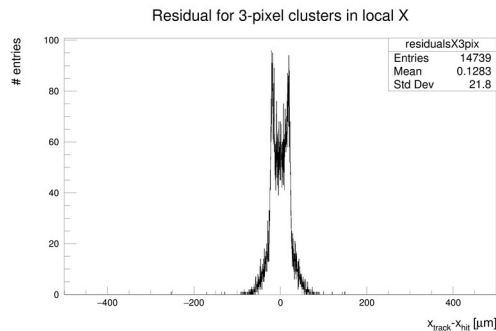
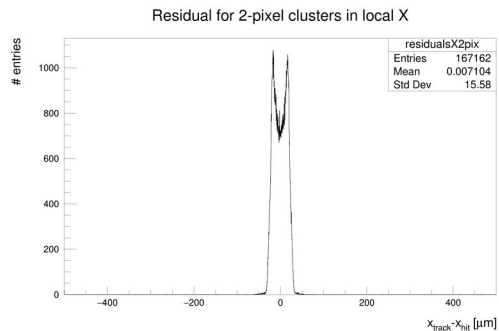
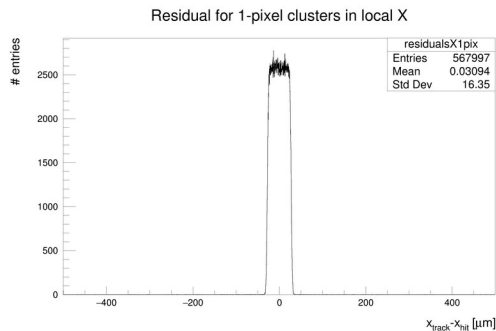
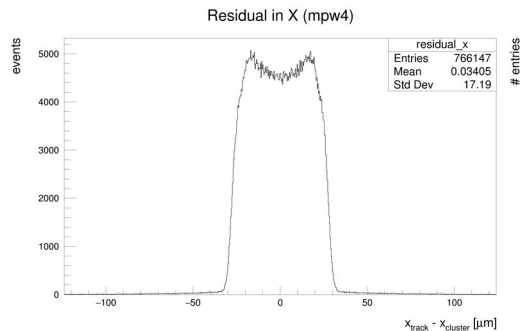
# Results Overview



Threshold

- Average Cluster-size  $\sim 1.3$  pixel / cluster
  - Testbeam result: 1.324 pixel / cluster
- Mean charge of  $20.6 \text{ ke}^-$  collected at pixels
  - First peak at  $\sim 3.5 \text{ ke}^-$  due to charge sharing
  - Cluster charge shows only 1 single peak

# Spatial resolution

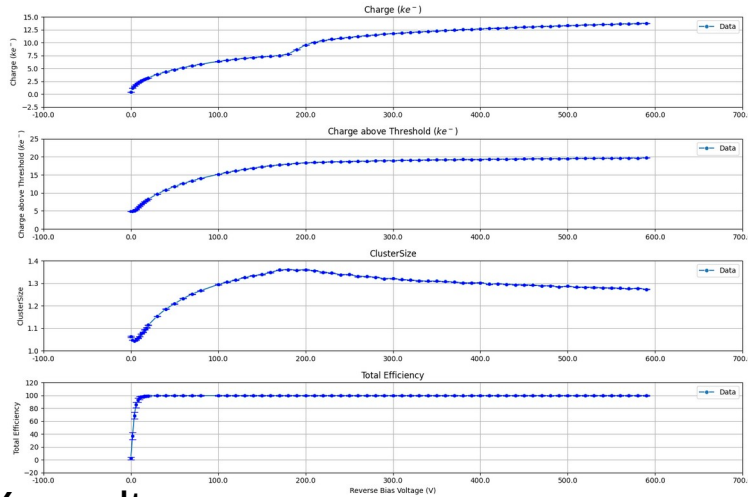


- Residuals show spatial resolution of
  - Total: 17.19µm
  - 1 Pix cluster: 16.35µm
  - 2 Pix cluster: 15.58µm
    - Significant double peak
  - 3 Pix cluster: 21.8µm
    - Significant double peak
- Double peak due to high threshold?
  - Shared charge not detected
- “Significant” differences to test-beam
  - We are using actual charge in  $e^-$  not ToT for center of gravity impact position



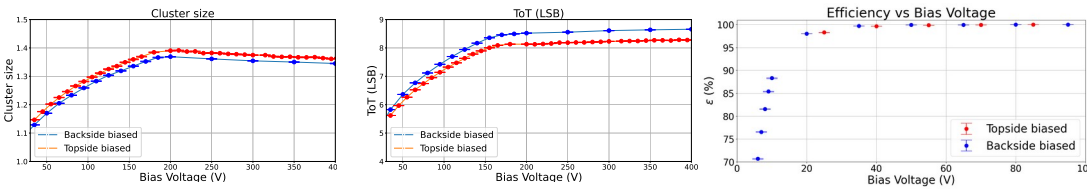
# Bias scan

Allpix<sup>2</sup>:

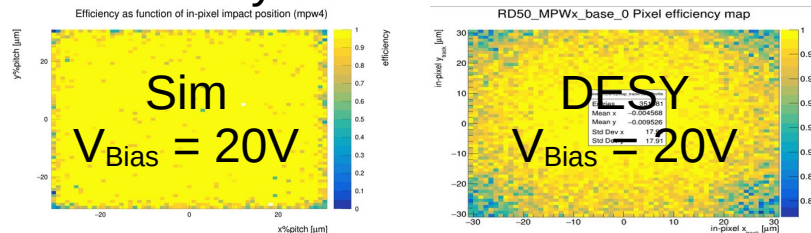


DESY results:

- Saturation of charge observed at  $V_{Bias} \rightarrow$  depletion voltage ( $V_{Depl}$  simulated with 200V)
- Cluster-size decreases at  $V_{Bias} > V_{depl}$
- Both in good agreement with testbeam results
- Simulation full efficient down to  $V_{Bias} \sim 10V$
- Test-beam shows degradation „already“ at  $V_{Bias} \sim 20V$ 
  - Linear approximation of E-field no longer valid
  - Test-beam results show strong corner effects

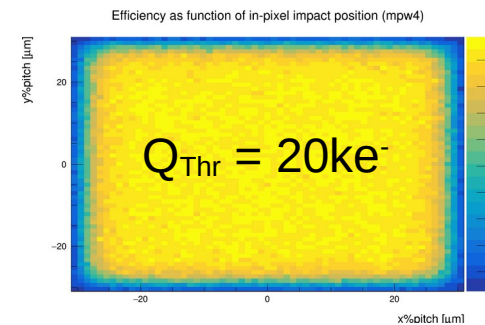
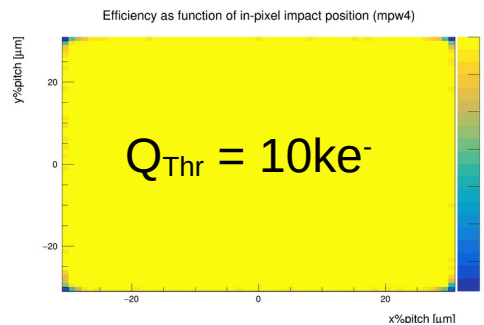
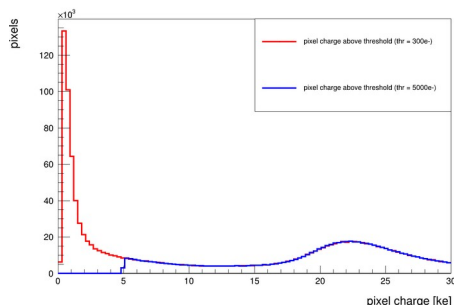
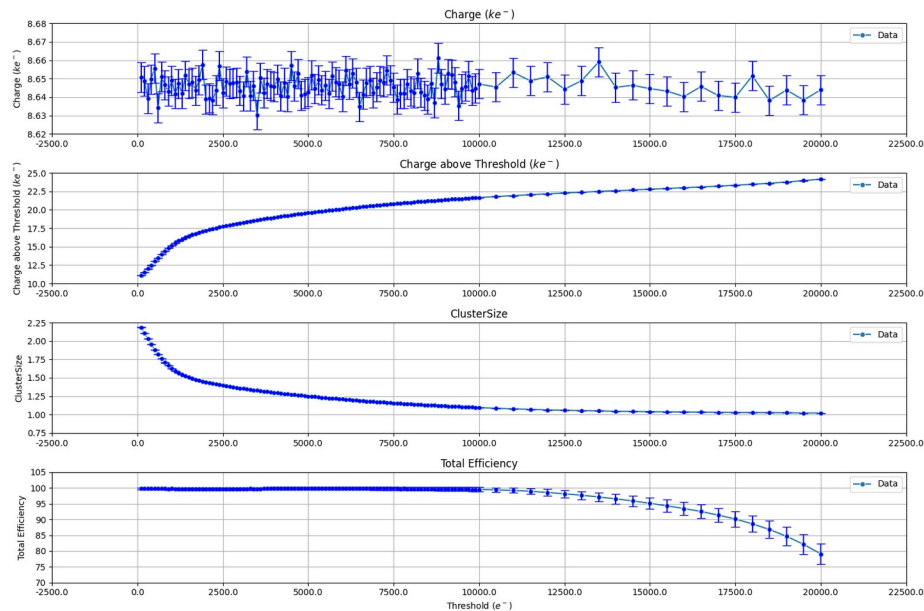


In-pixel efficiency:



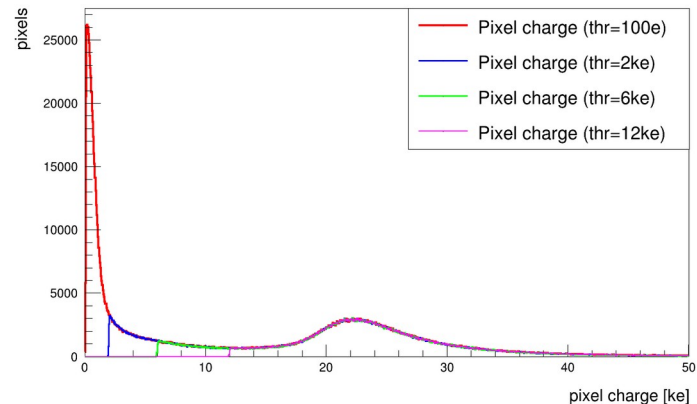
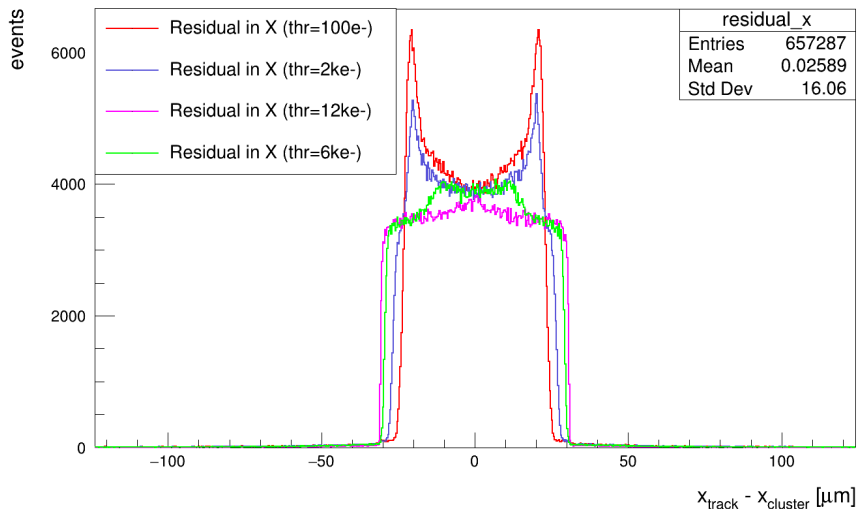
# Threshold scan

- Charge mostly unaffected
- Mean charge above threshold increases due to cut off of low charge signals
- Efficiency decreases only at  $\sim 10\text{ke}^-$ 
  - Test-beam shows decrease at  $\sim 5000e^-$
  - Again less severe corner effects in in-pixel-efficiency observed



# Threshold scan – Residuals

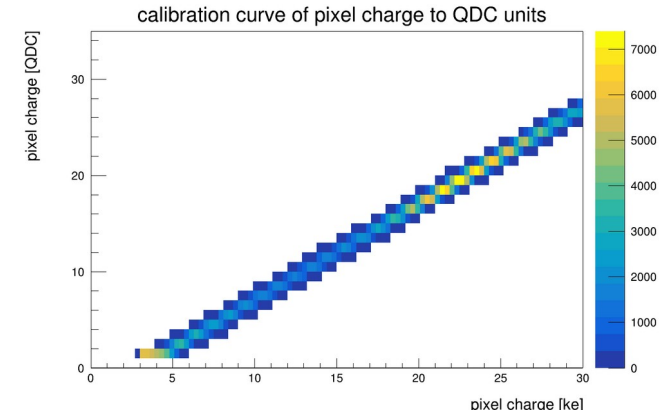
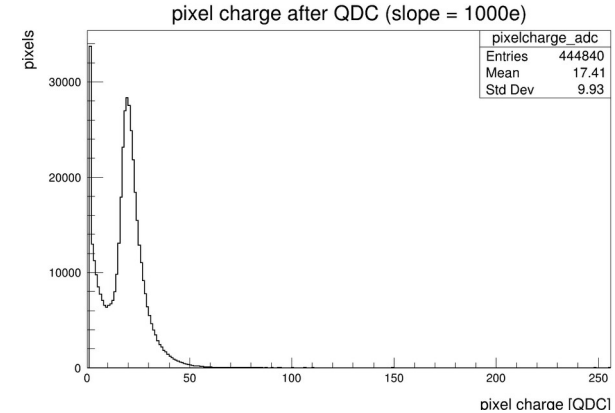
- Double peak characteristic less pronounced at higher thresholds
  - Less charge sharing



$Q_{thr}$ [e-]	Spatial resolution [ $\mu\text{m}$ ]
100	16.06
2k	16.82
6k	17.39
12k	17.75

## Introducing QDC → ToT

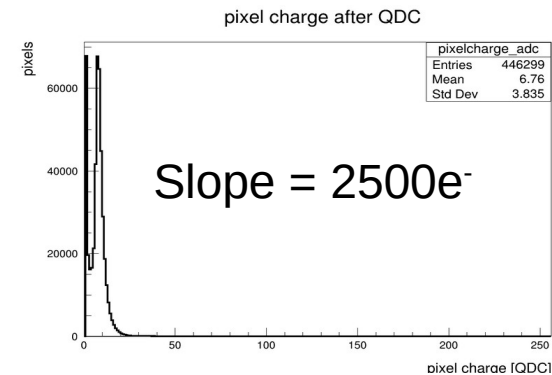
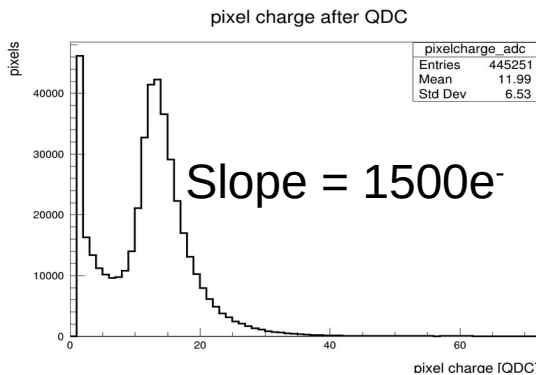
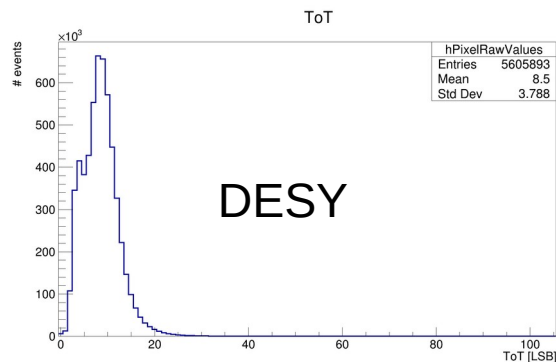
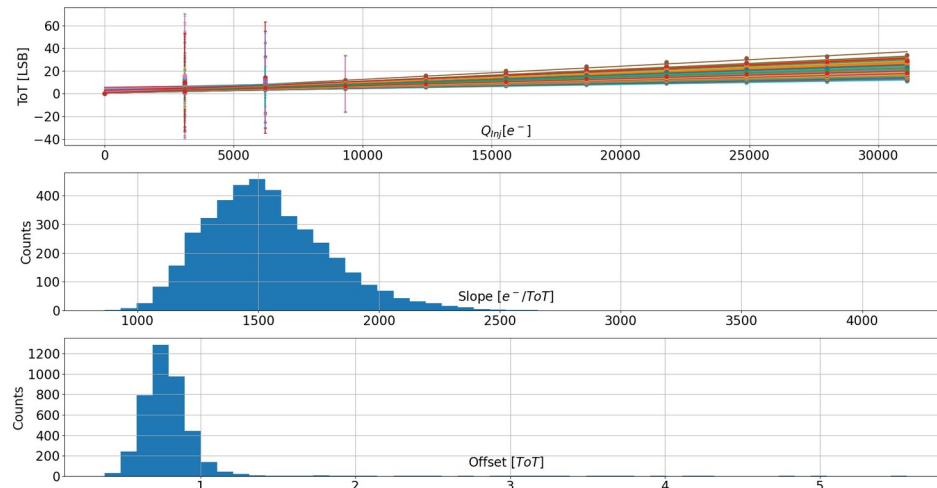
- In MPW4 data we have no actual charge but ToT
- What effect does this have on the observables? Also “easy access” benchmark
- Easiest way to simulate in Allpix<sup>2</sup>: introduce a QDC (charge to digital converter)
  - Number of bits (in our case 8)
  - QDC slope as slope of linear relation between Charge → ToT
- First peak at low QDC values again due to charge sharing



# Get QDC slope right

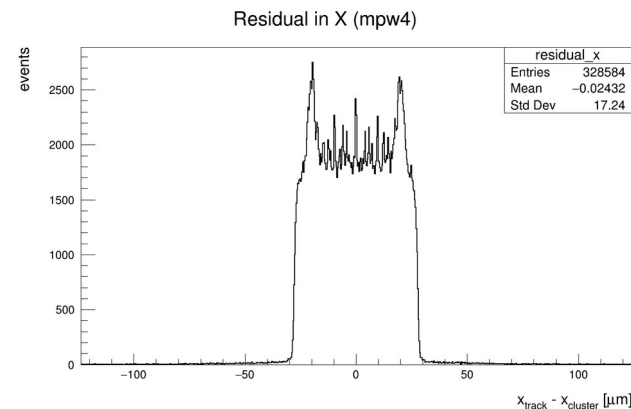
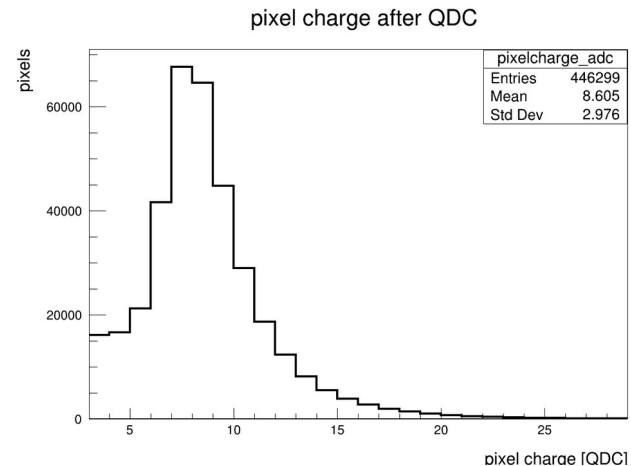
- How to get QDC slope right?
  - Lab evaluation inject into all pixels → fit to linear function → extract mean slope
    - Shows slope of  $\sim 1530e^-$
    - Ranging from  $1000 - 2500e^-$
  - Benchmark to test-beam results
    - Show average ToT of  $\sim 8.5\text{LSB}$  at  $Q_{\text{Thr}} \sim 3000e^-$

## Injection Scan



## QDC results

- QDC slope of  $2500e^-$  and cut first peak resembles ToT of test-beam result pretty good
- Residuals show only slightly worse spatial resolution compared to calculation with actual charge
  - Double peak more pronounced compared to simulation without QDC



## Summary / Outlook

- Most results of test-beam (at least right ball park) were reproduced in simple simulations
- Residuals show unexpected „shape“
  - Cut pixels with low charge
  - Disable diffusion
  - Increase track position uncertainty at DUT
  - Collect charges not on sensor surface but with actual (Deep N-well) implant
    - Requires E-field with lateral components → TCAD
- First (low ToT) peak not observed in DESY results
  - Is our threshold larger than we think?